

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (canceled)
2. (currently amended): The device according to claim [[1]] 20, wherein one of said first and second semiconductor substrates includes a light-emitting layer.
- 3-5. (canceled)
6. (currently amended): The device according to claim [[1]] 20, wherein said amorphous layer has a thickness of 1 nm or more.
7. (withdrawn): A manufacturing method of a semiconductor device, said method comprising:
  - a first step of pressing, onto each other, surfaces of first and second semiconductor substrates different in lattice constant, so that they are bonded to each other; and

a second step of treating, with heat, said first and second semiconductor substrates bonded, so as to form an amorphous layer at an interface between said first and second semiconductor substrates.

8. (withdrawn): The method of according to claim 7, wherein said first and second semiconductor substrates are treated at a temperature of 550 °C or higher for one hour or longer in said second step.

9. (withdrawn): The method according to claim 7, wherein one of said first and second semiconductor substrates includes a light-emitting layer.

10. (withdrawn): The method according to claim 7, wherein said first semiconductor substrate is an InP substrate including a compound semiconductor layer of zero layers or one or more layers and said second semiconductor substrate is a GaAs substrate including a compound semiconductor layer of zero layers or one or more layer.

11. (withdrawn): The method according to claim 10, wherein a compound semiconductor layer of said first semiconductor substrate is made of  $\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$  (x and y are numbers from zero to one).

12. (withdrawn): The method according to claim 10, wherein a compound semiconductor layer of said second semiconductor substrate is made of  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  (x is a number from zero to one).

13. (withdrawn): The method according to claim 7, wherein said amorphous layer has a thickness of 1 nm or more.

14. (canceled)

15. (currently amended): The device according to claim [[14]] 16, wherein one of said first and second semiconductor substrates includes a light-emitting layer.

16. (currently amended): ~~The device according to claim 14,~~ A semiconductor device comprising:

a first and second semiconductor substrates, both being different in lattice constant and bonded with each other,

wherein an interface between said first and second semiconductor substitutes has a linear current-voltage characteristic, and an amorphous layer made of constituent atoms of said first and second semiconductor substitutes is formed at said interface,

wherein said first semiconductor substrate is an InP substrate including a compound semiconductor layer of zero layers or one or more layers and said second semiconductor substrate is a GaAs substrate including a compound semiconductor layer of zero layers or one or more layers.

17. (previously presented): The device according to claim 16, wherein said compound semiconductor layer of said first semiconductor substrate is made of  $\text{In}_{1-x}\text{Ga}_x\text{As}_y\text{P}_{1-y}$  (x and y are numbers from zero to one).

18. (previously presented): The device according to claim 16, wherein said compound semiconductor layer of said second semiconductor substrate is made of  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  (x is a number from zero to one).

19. (currently amended): The device according to claim ~~[[14]]~~ 16, wherein said amorphous layer has a thickness of 1 nm or more.

20. (previously presented): A semiconductor device comprising:  
a first and second semiconductor substrates, both being different in lattice constant and bonded with each other,  
wherein said first semiconductor substrate is an InP substrate and said second semiconductor substrate is a GaAs substrate, and  
wherein an interface between said first and second semiconductor substrates has a linear current-voltage characteristic, and an amorphous layer made of constituent atoms of said first and second semiconductor substrates is formed at said interface.